

Hyun-Jong Chung

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

37
papers

2,249
citations

16
h-index

39
g-index

39
ext. papers

2,514
ext. citations

8.4
avg, IF

4.35
L-index

#	Paper	IF	Citations
37	Semiconductor-less vertical transistor with I/I of 10. <i>Nature Communications</i> , 2021 , 12, 1000	17.4	4
36	Growth of Multilayer Graphene with a Built-in Vertical Electric Field. <i>Chemistry of Materials</i> , 2020 , 32, 5142-5152	9.6	3
35	High-speed residue-free transfer of two-dimensional materials using PDMS stamp and water infiltration. <i>Current Applied Physics</i> , 2020 , 20, 1190-1194	2.6	1
34	Enhanced Gas Sensing Properties of Graphene Transistor by Reduced Doping with Hydrophobic Polymer Brush as a Surface Modification Layer. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 55493-55500	9.5	10
33	Large Temperature-Independent Magnetoresistance without Gating Operation in Monolayer Graphene. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 53134-53140	9.5	1
32	The evolution of surface cleanness and electronic properties of graphene field-effect transistors during mechanical cleaning with atomic force microscopy. <i>Nanotechnology</i> , 2019 , 30, 394003	3.4	5
31	Planar and van der Waals heterostructures for vertical tunnelling single electron transistors. <i>Nature Communications</i> , 2019 , 10, 230	17.4	29
30	Engineering performance of barristors by varying the thickness of WS ₂ . <i>Current Applied Physics</i> , 2017 , 17, 11-14	2.6	1
29	Fabricating in-plane transistor and memory using atomic force microscope lithography towards graphene system on chip. <i>Carbon</i> , 2016 , 96, 223-228	10.4	11
28	Patterning of periodic ripples in monolayer MoS ₂ by using laser irradiation. <i>Journal of the Korean Physical Society</i> , 2016 , 69, 1505-1508	0.6	4
27	Origin of the channel width dependent field effect mobility of graphene field effect transistors. <i>Microelectronic Engineering</i> , 2016 , 163, 55-59	2.5	4
26	Nonuniform current distribution between individual layers of multilayer MoS ₂ , experimentally approached by using a laser thinning technique. <i>Journal of the Korean Physical Society</i> , 2016 , 69, 1497-1501	0.6	5
25	Engineering Optical and Electronic Properties of WS ₂ by Varying the Number of Layers. <i>ACS Nano</i> , 2015 , 9, 6854-60	16.7	73
24	Is quantum capacitance in graphene a potential hurdle for device scaling?. <i>Nano Research</i> , 2014 , 7, 453-461	4.0	8
23	Step-by-step implementation of an amplifier circuit with a graphene field-effect transistor on a printed-circuit board. <i>Current Applied Physics</i> , 2014 , 14, 1057-1062	2.6	8
22	Random telegraph noise in metallic single-walled carbon nanotubes. <i>Applied Physics Letters</i> , 2014 , 104, 193102	3.4	2
21	Electrical control of kinesin-microtubule motility using a transparent functionalized-graphene substrate. <i>Nanotechnology</i> , 2013 , 24, 195102	3.4	12

20	Low temperature growth of complete monolayer graphene films on Ni-doped copper and gold catalysts by a self-limiting surface reaction. <i>Carbon</i> , 2013 , 64, 315-323	10.4	29
19	Graphene for true Ohmic contact at metal-semiconductor junctions. <i>Nano Letters</i> , 2013 , 13, 4001-5	11.5	81
18	Graphene and thin-film semiconductor heterojunction transistors integrated on wafer scale for low-power electronics. <i>Nano Letters</i> , 2013 , 13, 5967-71	11.5	56
17	Transparent Graphene Electrodes for Highly Efficient III/V Multijunction Concentrator Solar Cells. <i>Energy Technology</i> , 2013 , 1, 283-286	3.5	
16	Compact modeling of extremely scaled graphene FETs. <i>Journal of the Korean Physical Society</i> , 2012 , 61, 1797-1801	0.6	3
15	Graphene barristor, a triode device with a gate-controlled Schottky barrier. <i>Science</i> , 2012 , 336, 1140-3	33.3	748
14	Graphene for metal-semiconductor Ohmic contacts 2012 ,		3
13	Integration of high quality top-gated graphene field effect devices on 150 mm substrate 2011 ,		2
12	Fast transient charging at the graphene/SiO ₂ interface causing hysteretic device characteristics. <i>Applied Physics Letters</i> , 2011 , 98, 183508	3.4	113
11	A role for graphene in silicon-based semiconductor devices. <i>Nature</i> , 2011 , 479, 338-44	50.4	556
10	Enhanced Current Drivability of CVD Graphene Interconnect in Oxygen-Deficient Environment. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1591-1593	4.4	19
9	Passivation of metal surface states: microscopic origin for uniform monolayer graphene by low temperature chemical vapor deposition. <i>ACS Nano</i> , 2011 , 5, 1915-20	16.7	54
8	Band gap opening by two-dimensional manifestation of peierls instability in graphene. <i>ACS Nano</i> , 2011 , 5, 2964-9	16.7	53
7	Robust bi-stable memory operation in single-layer graphene ferroelectric memory. <i>Applied Physics Letters</i> , 2011 , 99, 042109	3.4	133
6	Characteristics of CVD graphene nanoribbon formed by a ZnO nanowire hardmask. <i>Nanotechnology</i> , 2011 , 22, 295201	3.4	26
5	RF performance of pre-patterned locally-embedded-back-gate graphene device 2010 ,		10
4	Large-grained and Highly-ordered Graphene Synthesized by Radio Frequency Plasma-enhanced Chemical Vapor Deposition. <i>ECS Transactions</i> , 2009 , 19, 111-114	1	8
3	Radio-Frequency Electrical Characteristics of Single Layer Graphene. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 091601	1.4	24

- 2 The structural and electrical evolution of graphene by oxygen plasma-induced disorder.
Nanotechnology, **2009**, 20, 375703 3-4 86
- 1 Real-time evolution of trapped charge in a SiO₂ layer: An electrostatic force microscopy study.
Applied Physics Letters, **2001**, 79, 2010-2012 3-4 62